



60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
60V	$50m\Omega$ @ $V_{GS} = 10V$	24A
607	65mΩ @ V _{GS} = 4.5 V	21A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

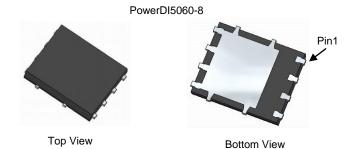
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

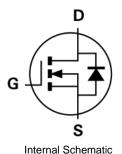
Features and Benefits

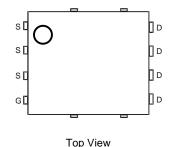
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_g Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: PowerDI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.097 grams (Approximate)







Pin Configuration

Ordering Information (Note 5)

Part Number		Case	Packaging	
	DMNH6042SPSQ-13	PowerDI5060-8	2500/Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



);; = Manufacturer's Marking
NH6042SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 16 = 2016)
WW = Week (01 to 53)



Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 8) $V_{GS} = 10V$ Steady $T_{C} = +25^{\circ}C$ State $T_{C} = +100^{\circ}C$			I _D	24 17	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	35	Α		
Maximum Continuous Body Diode Forward Current (Is	24	Α		
Avalanche Current (Note 9) L = 10mH			I _{AS}	3.5	Α
Avalanche Energy (Note 9) L = 10mH			Eas	65	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)		P _D	1.5	W
Thermal Desistance I has time to Architect (Note C)	Steady state	<u> </u>	98	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	54	
Total Power Dissipation (Note 7)		P _D	2.9	W
The word Designation to Applicat (Note 7)	Steady state	<u> </u>	51	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	t<10s	$R_{\theta JA}$	26	
Thermal Resistance, Junction to Case (Note 8)		$R_{\theta JC}$	3.5	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

<u></u>							
Characteristic		Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)							
Drain-Source Breakdown Voltage		60		_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	-	_	1	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 10)							
Gate Threshold Voltage	V _{GS(TH)}	1.0	1	3.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance		I	34	50	mΩ	$V_{GS} = 10V, I_D = 5.1A$	
Static Dialit-Source Off-Resistance	R _{DS(ON)}	1	45	65	11122	$V_{GS} = 4.5V, I_D = 4.4A$	
Diode Forward Voltage	V_{SD}	l	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 2.6A$	
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	Ciss	1	584	_	pF	\/ 25\/ \/ 0\/	
Output Capacitance	Coss	l	83	_	pF	$V_{DS} = 25V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	Crss	I	24	_	pF	1 – 1.0101112	
Gate Resistance		I	3.8	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)		I	4.2	_	nC		
Total Gate Charge (V _{GS} = 10V)		I	8.8	_	nC	V _{DS} = 44V. I _D = 5.2A	
Gate-Source Charge	Q_{gs}	I	1.8	_	nC	$V_{DS} = 44V, I_{D} = 5.2A$	
Gate-Drain Charge	Q_{gd}	1	1.8	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	3.4	_	ns		
Turn-On Rise Time	t _R	_	1.9	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	10.1	_	ns	$R_G = 6\Omega$, $I_D = 1A$	
Turn-Off Fall Time	t _F	_	4.5	_	ns]	
Body Diode Reverse Recovery Time			12.9	_	ns	I _F = 2.6A, di/dt = 100A/μs	
Body Diode Reverse Recovery Charge		_	5.4	_	nC	$I_F = 2.6A$, $di/dt = 100A/\mu s$	

6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

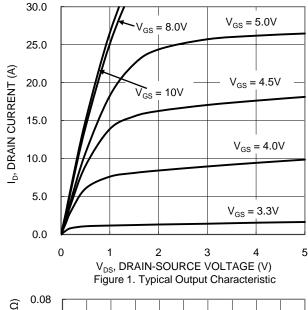
PowerDI is a registered trademark of Diodes Incorporated. DMNH6042SPSQ Document number: DS38709 Rev. 1 - 2

^{7.} Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

^{8.} Thermal resistance from junction to soldering point (on the exposed drain pad).

I. Is and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





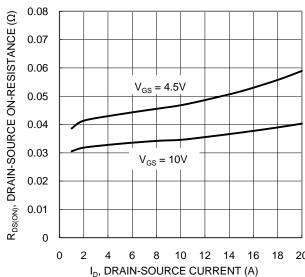


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

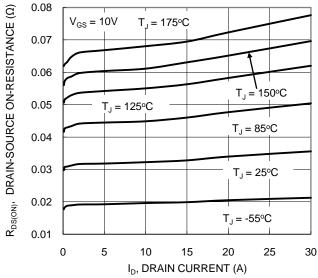
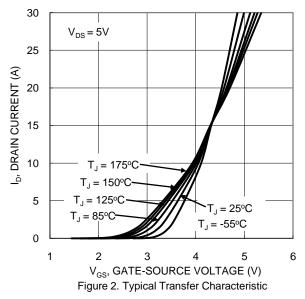
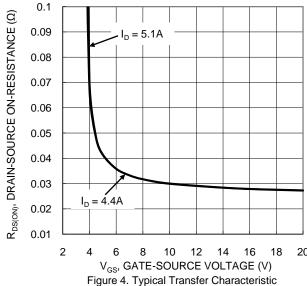


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





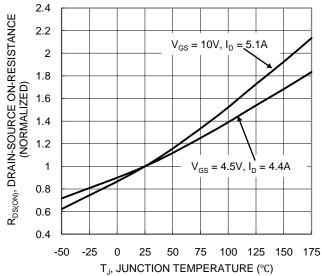
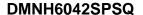
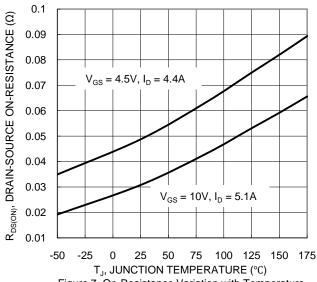
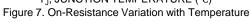


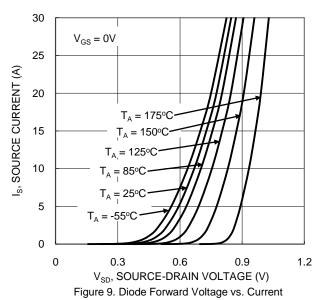
Figure 6. On-Resistance Variation with Temperature

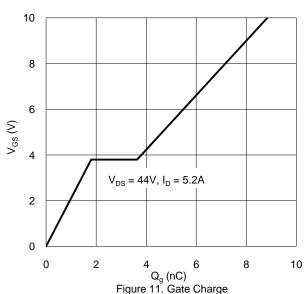












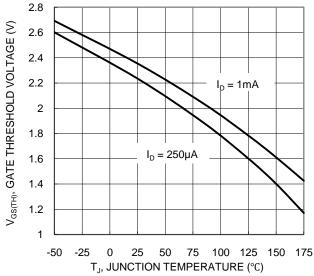
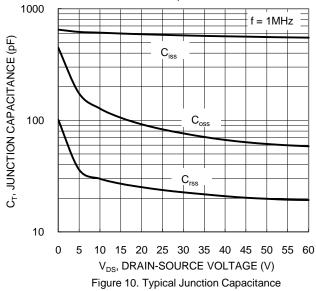
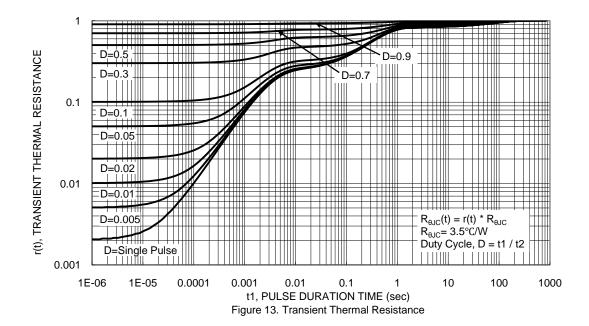


Figure 8. Gate Threshold Variation vs. Junction Temperature



100 $R_{DS(ON)}$ Limited 10 ID, DRAIN CURRENT (A) P_w=10ms 1 P_W=100ms $T_{J(Max)} = 175$ °C 0.1 $T_C = 25^{\circ}C$ Single Pulse DUT on infinite heatsink V_{GS}=10V 0.01 0.1 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



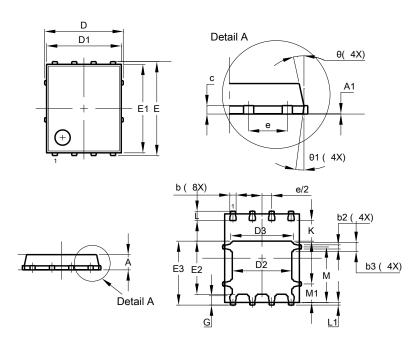




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

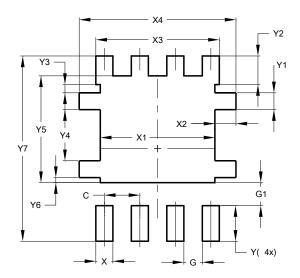


PowerDI5060-8					
Dim	Min Max Typ				
Α	0.90	1.00			
A1	0.00 0.05 -				
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D	,	5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	(6.15 BSC	;		
E1	5.60	5.60 6.00 5.8			
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12º	11º		
Θ1	6º	8º	7º		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Υ	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610



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